

MICRO ELECTRONICS

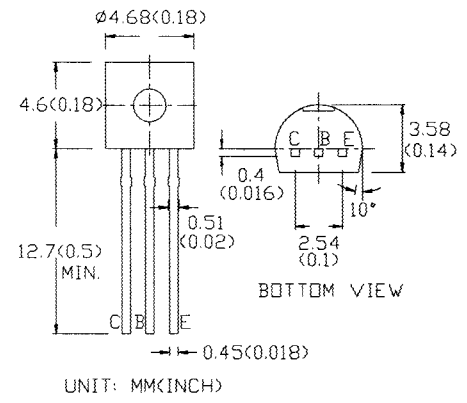
MPS6512S

**NPN
SILICON
TRANSISTOR**

TO-92A

DESCRIPTION

MPS6512S is NPN silicon planar transistors designed for general purpose amplifier applications.



ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	VCBO	40V
Collector-Emitter Voltage	VCEO	30V
Emitter-Base Voltage	VEBO	4V
Collector Current	IC	100mA
Continuous Power Dissipation	Pd	350mW
Operating & Storage Junction Temperature	Tj, Tstg	-55 to +150°C

ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	CONDITIONS
Collector-Emitter Breakdown Voltage	BVCEO	30		V	IC=0.5mA IB=0
Emttter-Base Breakdown Voltage	BVEBO	4		V	IE=10μA IC=0
Collector Cutoff Current	ICBO		50	nA	VCB=30V IE=0
D.C. Current Gain	HFE*	50	120		IC=2mA VCE=10V
		30			IC=100mA VCE=10V
Collector-Emitter Saturation Voltage	VCE(sat)		0.5	V	IC=50mA IB=5mA
Current Gain Bandwidth Product	fT	150	TYP	MHz	IC=2mA VCE=10V
					f=20MHz
Output Capacitance	Cob		3.5	pF	VCB=10V f=1MHz
Noise Figure	NF	2	TYP	dB	IC=10μA VCE=5V
					Rs=10Kohm f=1kHz

* Pulse test : pulse width <300μS, duty cycle < 2%.



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